

# Medium power transistor (−32V, −2A)

2SB1182 / 2SB1240

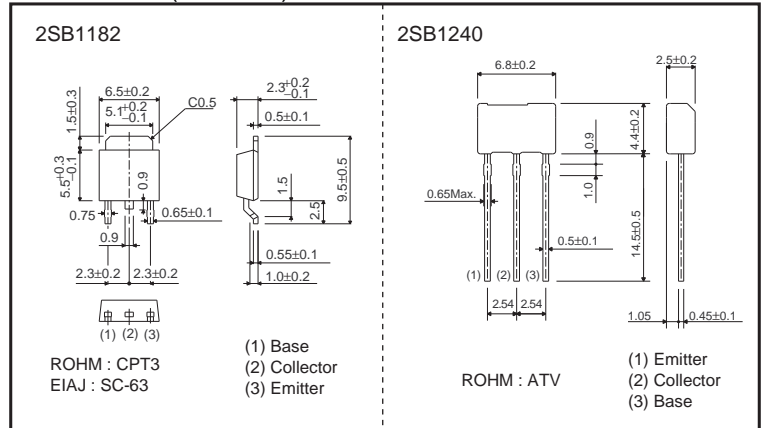
●Features

- 1) Low  $V_{CE(sat)}$ .  
 $V_{CE(sat)} = -0.5V$  (Typ.)  
 $(I_C/I_B = -2A / -0.2A)$
- 2) Complements 2SD1758 / 2SD1862.

●Structure

Epitaxial planar type  
PNP silicon transistor

●Dimensions (Unit : mm)



●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Collector-base voltage	$V_{CBO}$	-40	V
Collector-emitter voltage	$V_{CEO}$	-32	V
Emitter-base voltage	$V_{EBO}$	-5	V
Collector current	$I_C$	-2	A(DC)
		-3	A (Pulse) *1
Collector power dissipation	2SB1182	10	W (Tc=25°C)
	2SB1240		
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-55 to 150	°C

\*1 Single pulse, Pw=100ms

\*2 Printed circuit board, 1.7mm thick, collector copper plating 100mm<sup>2</sup> or larger.

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Collector-base breakdown voltage	$BV_{CBO}$	-40	-	-	V	$I_C = -50\mu A$
Collector-emitter breakdown voltage	$BV_{CEO}$	-32	-	-	V	$I_C = -1mA$
Emitter-base breakdown voltage	$BV_{EBO}$	-5	-	-	V	$I_E = -50\mu A$
Collector cutoff current	$I_{CBO}$	-	-	-1	$\mu A$	$V_{CB} = -20V$
Emitter cutoff current	$I_{EBO}$	-	-	-1	$\mu A$	$V_{EB} = -4V$
Collector-emitter saturation voltage	$V_{CE(sat)}$	-	-0.5	-0.8	V	$I_C/I_B = -2A / -0.2A$ *
DC current transfer ratio	$h_{FE}$	120	-	390	-	$V_{CE} = -3V, I_C = -0.5A$ *
Transition frequency	$f_T$	-	100	-	MHz	$V_{CE} = -5V, I_E = 0.5A, f = 100MHz$
Output capacitance	$C_{ob}$	-	50	-	pF	$V_{CB} = -10V, I_E = 0A, f = 1MHz$

\* Measured using pulse current.

●Packaging specifications and hFE

Type	hFE	Package	Taping	
		Code	TL	TV2
		Basic ordering unit (pieces)	2500	2500
2SB1182	QR		○	—
2SB1240	QR		—	○

hFE values are classified as follows :

Item	Q	R
hFE	120 to 270	180 to 390

●Electrical characteristic curves

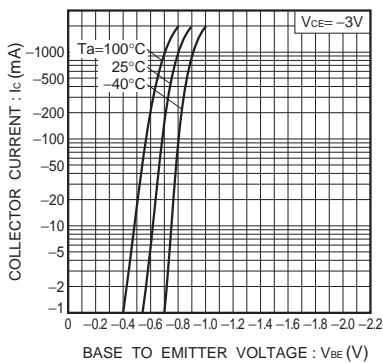


Fig.1 Grounded emitter propagation characteristics

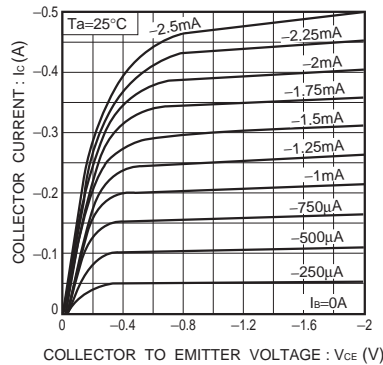


Fig.2 Grounded emitter output characteristics

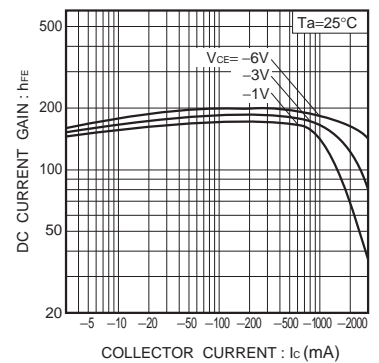


Fig.3 DC current gain vs. collector current (I)

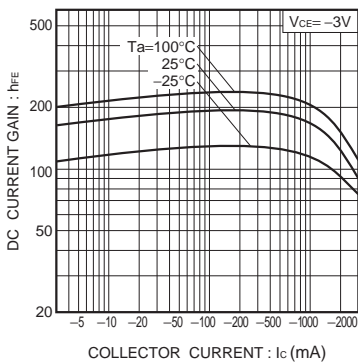


Fig.4 DC current gain vs. collector current (II)

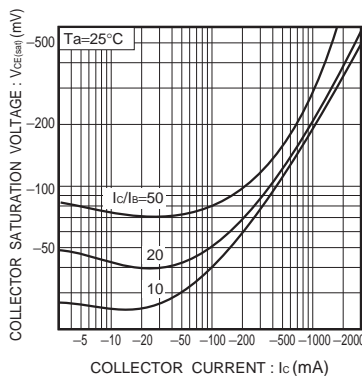


Fig.5 Collector-emitter saturation voltage vs. collector current (I)

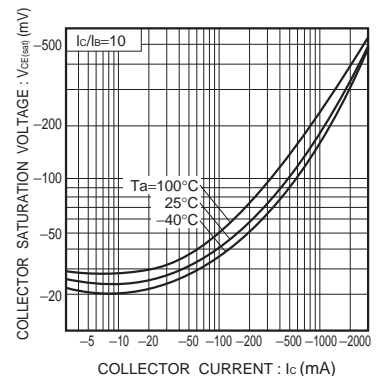


Fig.6 Collector-emitter saturation voltage vs. collector current (II)

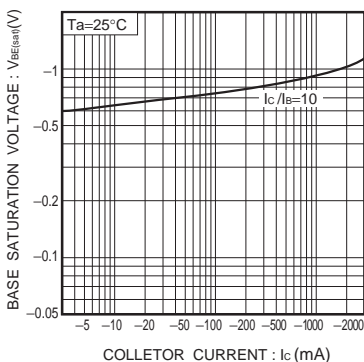


Fig.7 Base-emitter saturation voltage vs. collector current

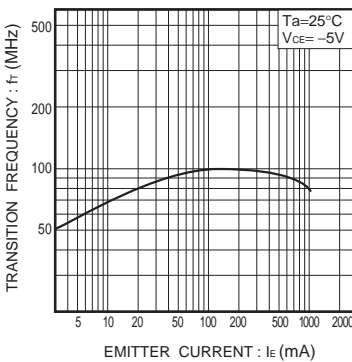


Fig.8 Gain bandwidth product vs. emitter current

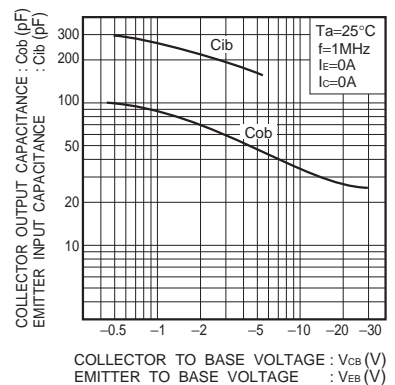


Fig.9 Collector output capacitance vs. collector-base voltage  
Emitter input capacitance vs. emitter-base voltage

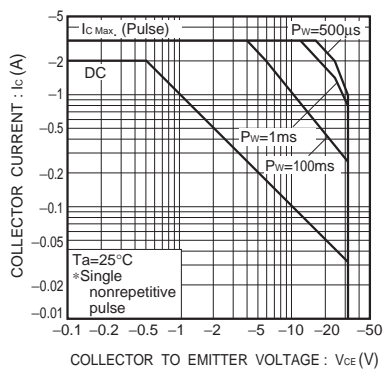


Fig.10 Safe operation area (2SB1182)

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